

Linearization Techniques for Power Amplifiers at the Device and Circuit Level (invited)

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DIMES

Introduction

Improving for the linearity/efficiency trade-off
is complex!

(it involves system, circuit & process technology considerations;)

Required:

knowledge of device non-linearities

+

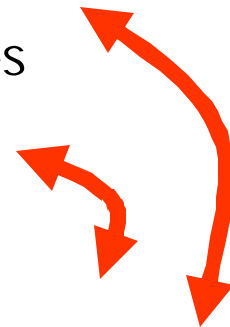
Profound knowledge of RF circuit design

+

Non-linear RF characterization tools & models

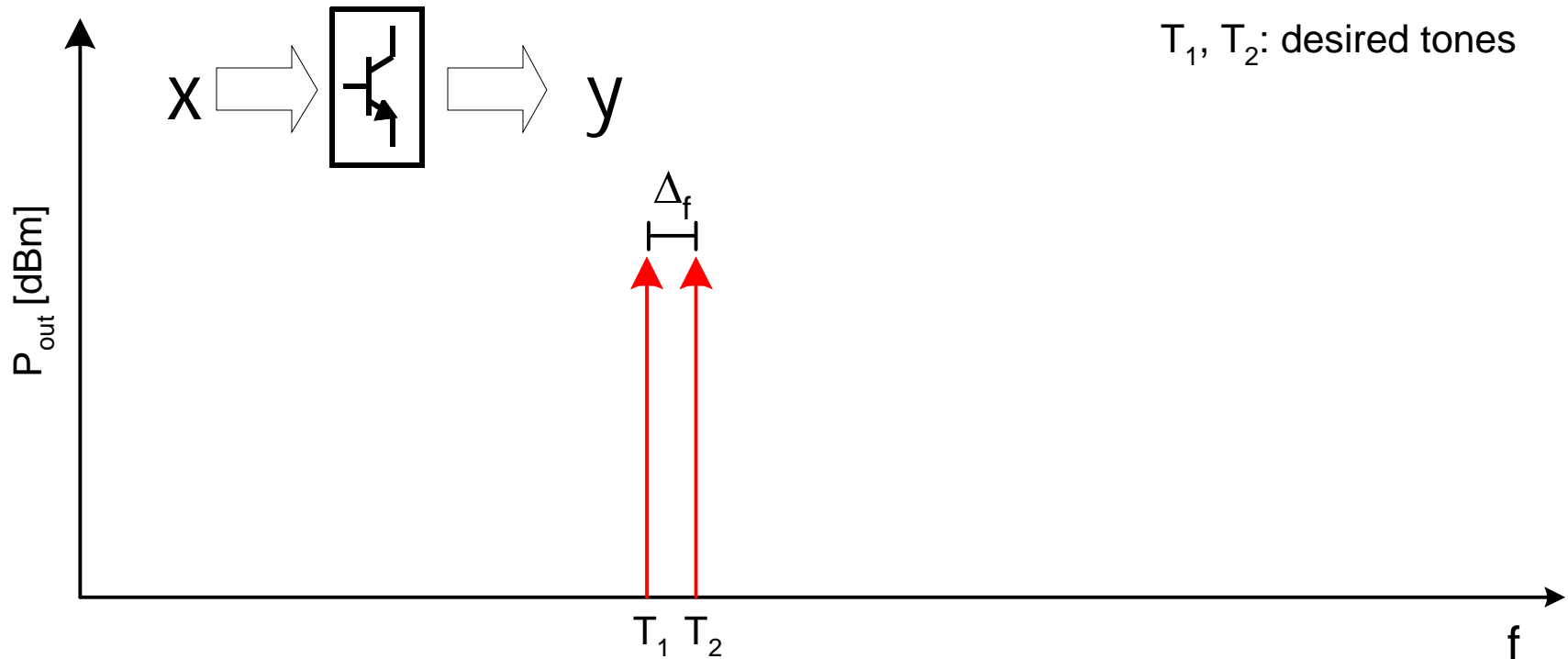
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Improved Circuit & Technology Design for Linearity



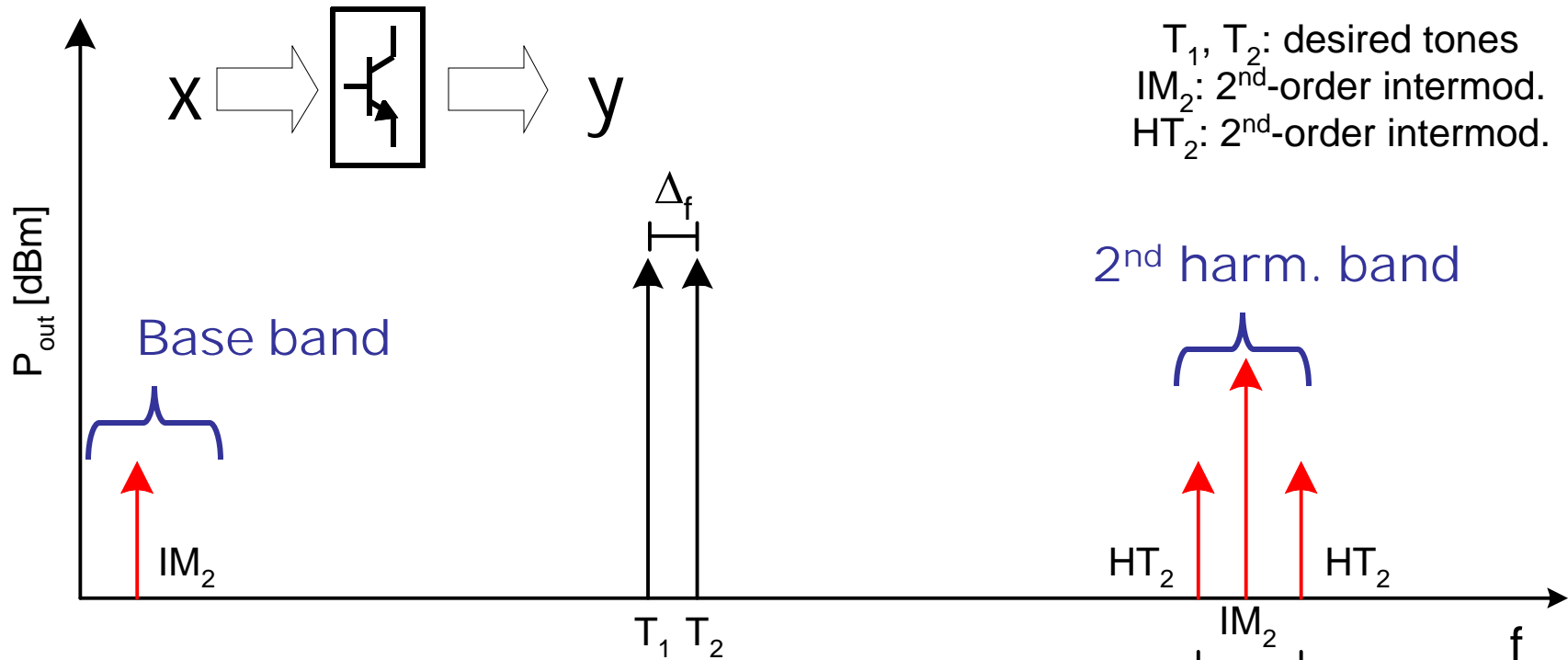
Introduction: Linearization Basics

$$y = a_1 x \text{ (linear response)}$$



Introduction: Linearization Basics

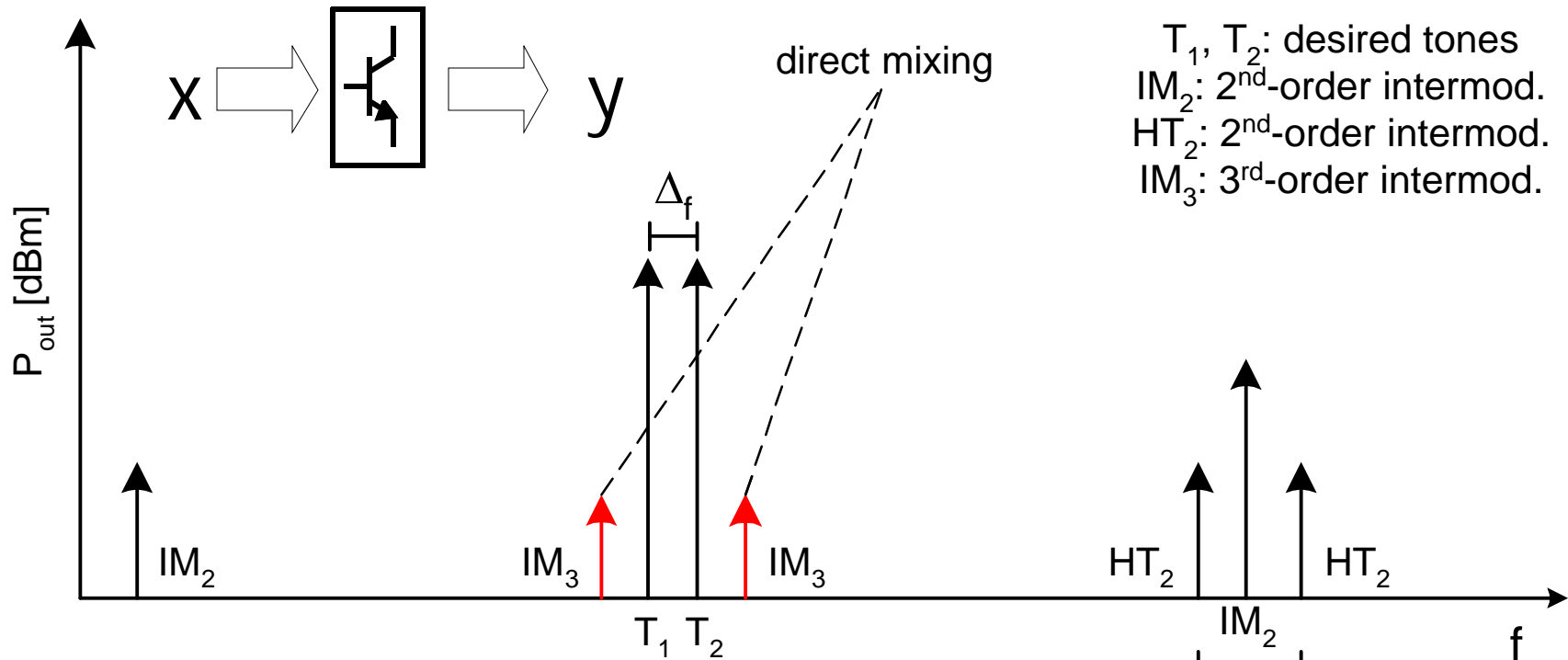
$$y = ax + a_2x^2 \text{ (2}^{\text{nd}}\text{-order intermod.)}$$



T_1, T_2 : desired tones
 IM_2 : 2nd-order intermod.
 HT_2 : 2nd-order intermod.

Introduction: Linearization Basics

$$y = ax + a_2x^2 + a_3x^3 \text{ (3rd-order intermod.)}$$

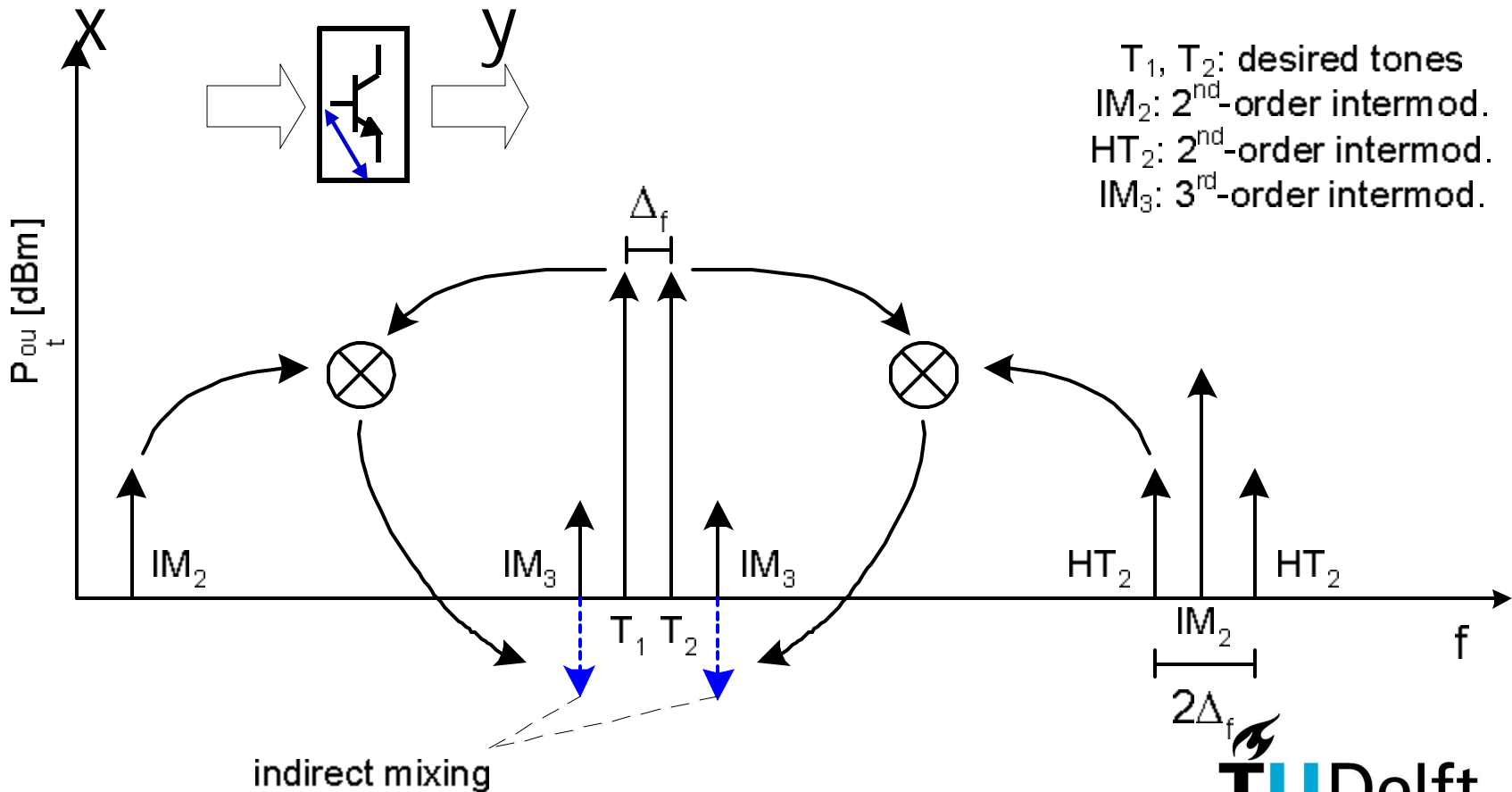


T_1, T_2 : desired tones
 IM_2 : 2nd-order intermod.
 HT_2 : 2nd-order intermod.
 IM_3 : 3rd-order intermod.

Introduction: Linearization Basics

$$y = ax_1 + a_2x^2 + a^3x^3$$

Indirect mixing

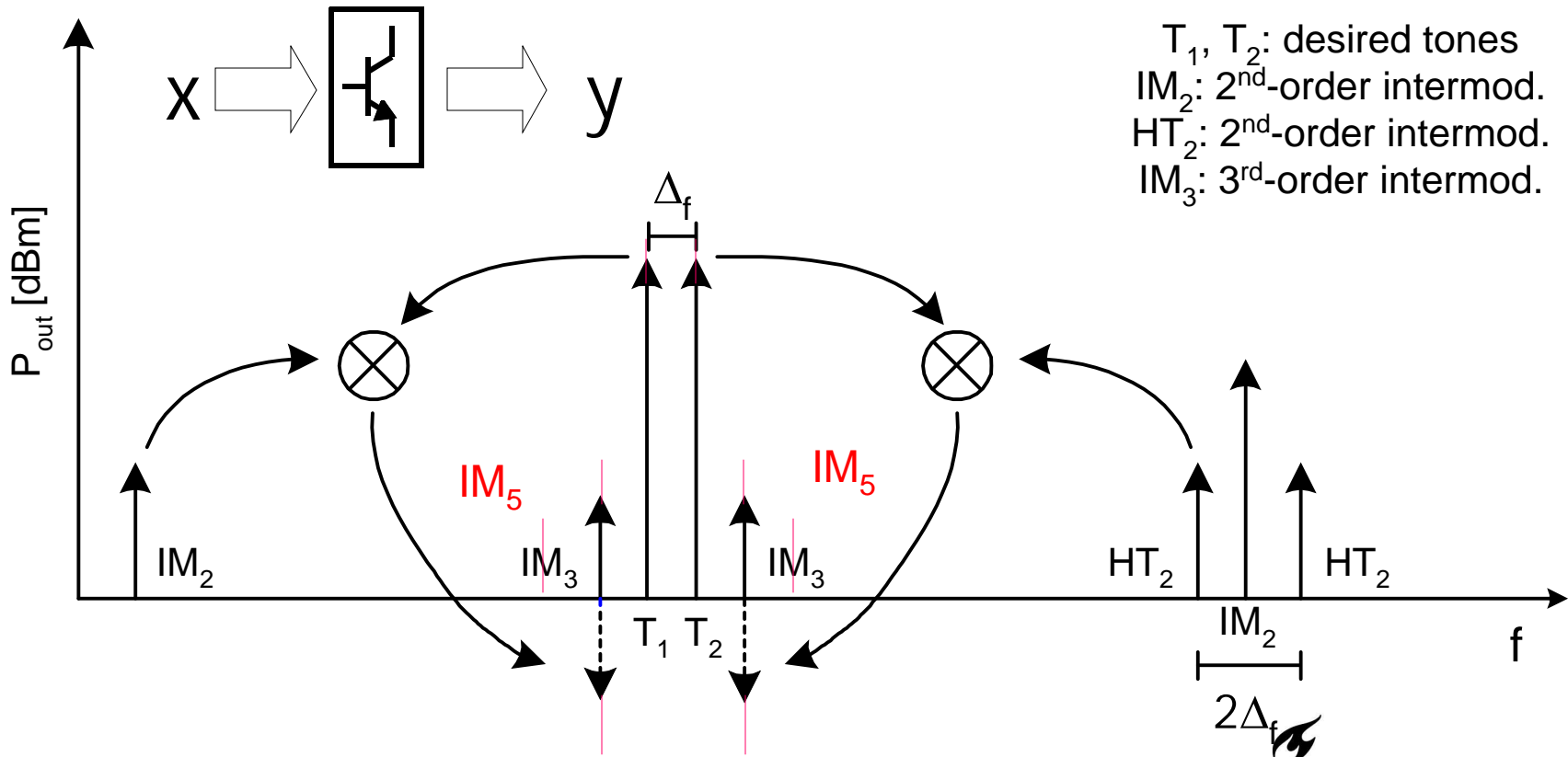


Introduction: Linearization Basics

$$y = ax_1 + a_2x^2 + a^3x^3 + \dots \text{ Higher order terms (x)}$$

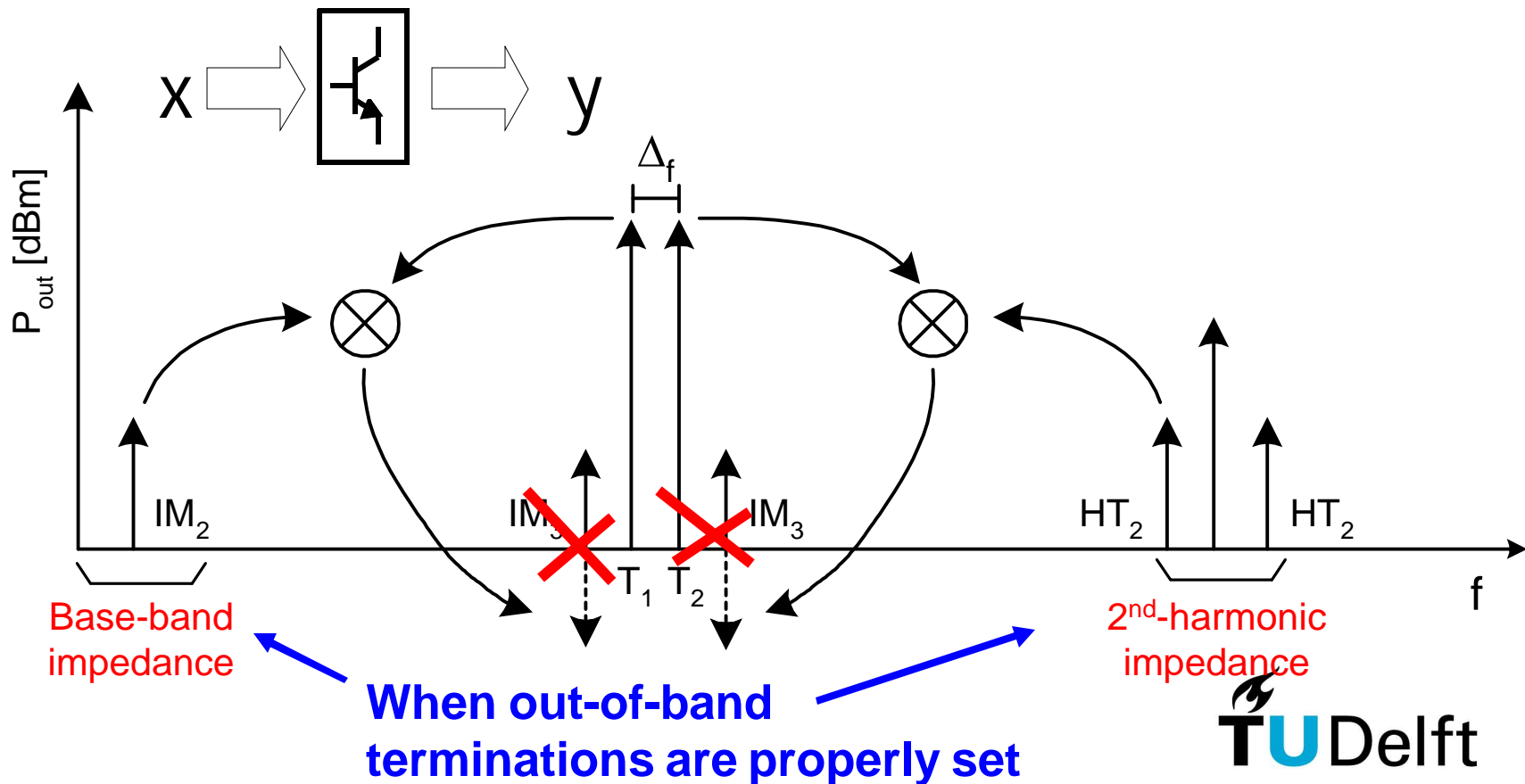
Low power

High power



Introduction: Linearization Basics

- **IM₃ cancellation** is achieved when direct and indirect products have equal amplitude and opposite phase, this can be controlled by the out-of-band impedances.



Overview

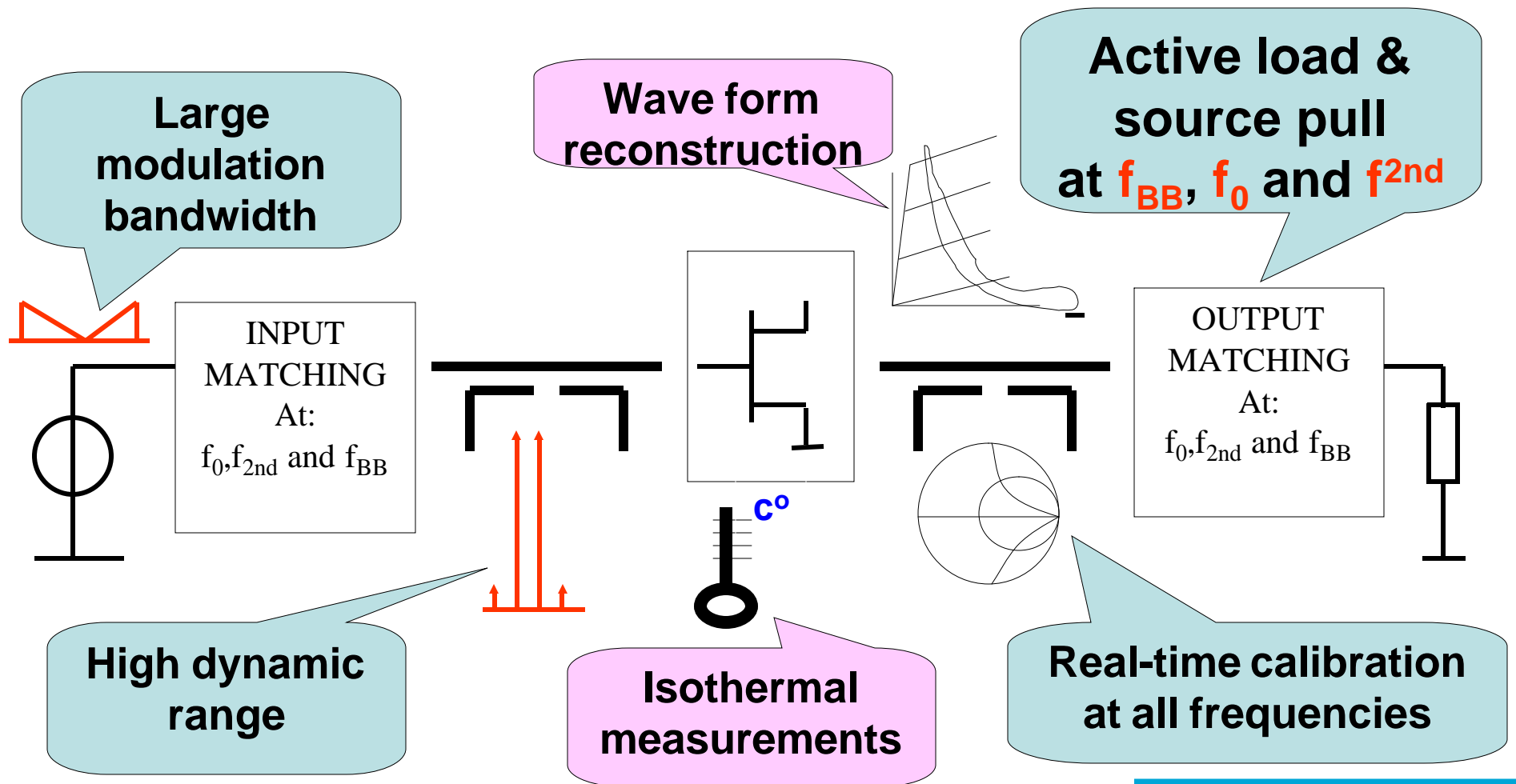
- Introduction
- Characterization
- Predictive Modeling & Device Optimization
- BJT based PA design
- FET based PA design
- Conclusions
- Outlook: Adaptive PA's
- Acknowledgements

Characterization

Large Signal Device Characterization setups at the TUDELFT
(custom-built)

- Isothermal measurements
(Data base model extraction / model verification)
- Differential load-pull measurements
(testing differential PA's)
- On-Wafer Active harmonic load-pull measurements
(Linearity optimization using out-of-band terminations)
(Evaluation Linearity new process generations)

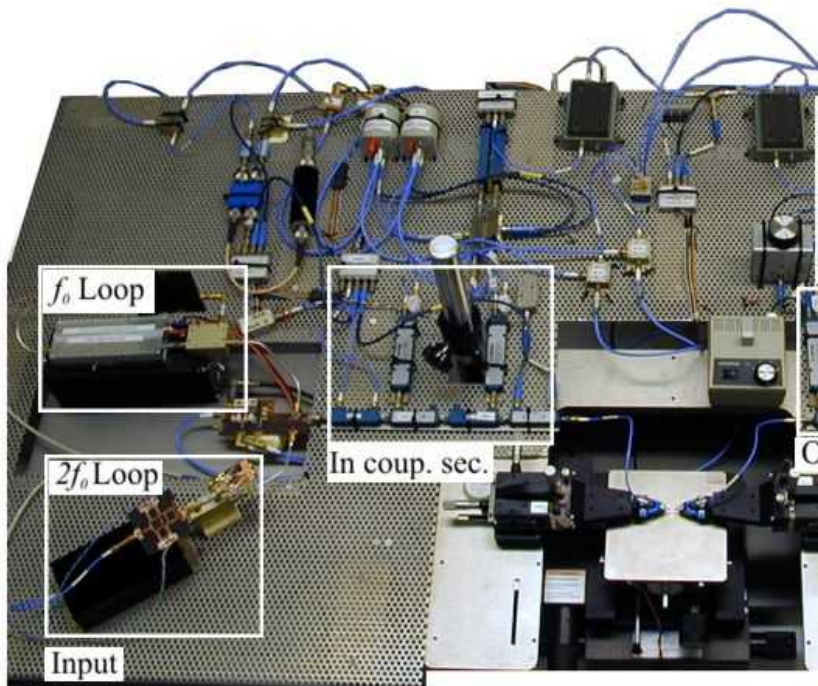
Characterization: Active Load-Pull setup, Principle



Novel setup for on-wafer non-linear device characterization using optimum circuit conditions

Characterization: Active Harmonic Load-Pull System

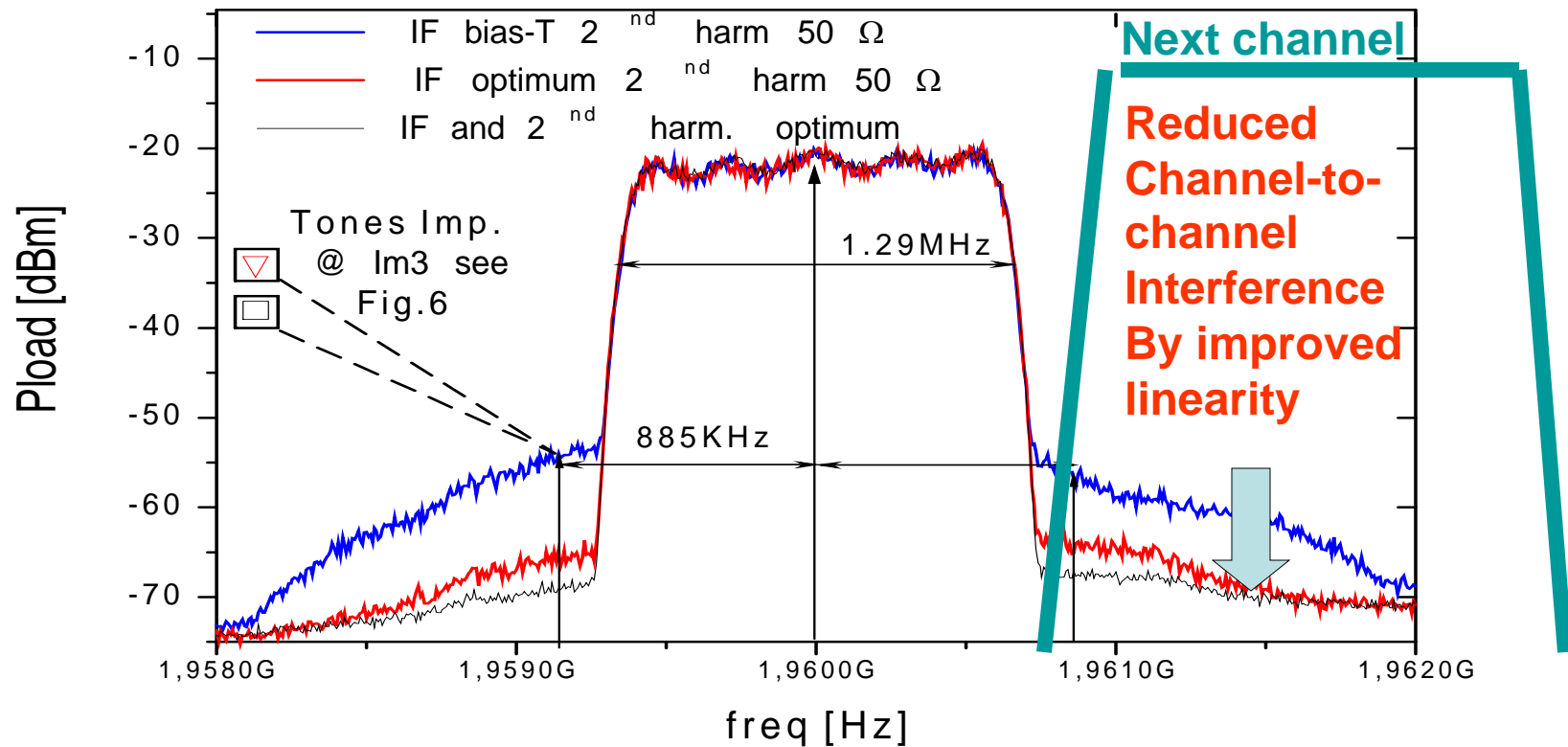
On wafer large-signal
device characterization!!!



Happy supporters from
Industry

Thesis work M. Spirito + support by Marco Pelk

Characterization: Active Harmonic Load-Pull System



Linearity imp. using optimum 2nd and IF impedances for an IS-95 signal.

On-wafer testing of device linearity using:

- optimum harmonic terminations
- wideband modulated signals

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Predictive Modeling & Device Optimization

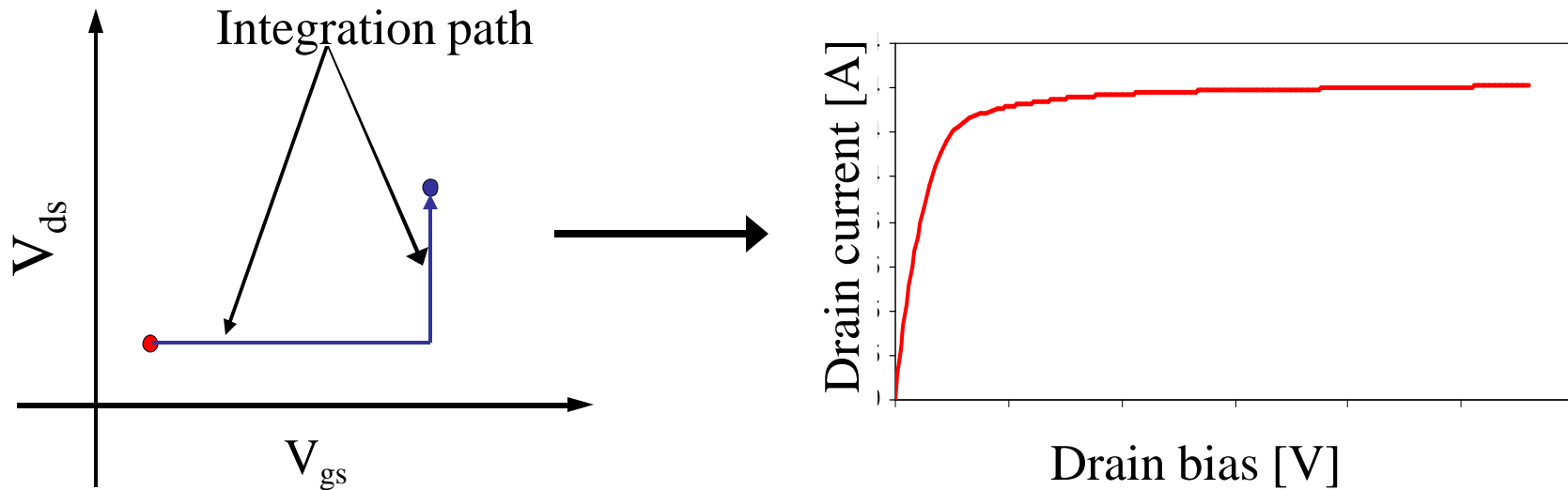
Smoothie

	Compact models	Mixed level models	Database models
Advantages	+ Speed + Accuracy + Physically based Mextram	+ Suitable for device innovation + Physically based	+ Device innovation + Meas./sim. based + Speed + Accuracy + very physical
Disadvantages	- Difficult to extract - No device innovation	+/- Accuracy - Not meas. based - Speed MAIDS	- Speed

Vittorio Cuomo

Predictive Modeling & Device Optimization

Smoothie model principles: Currents & charges
as line integral of the y-parameters over bias:



- ✓ Consistency between DC, AC and HB simulations!
 - ✓ Increased order of continuity
- But what about rotation and thermal effects?**

Predictive Modeling & Device Optimization

The database model Smoothie

Smoothie schematic

Blanked to avoid pre-publication

Large signal equivalent circuit Smoothie, including:

- dynamic thermal effects
- improved freq. dependency

→ Solves for the rotation problem!

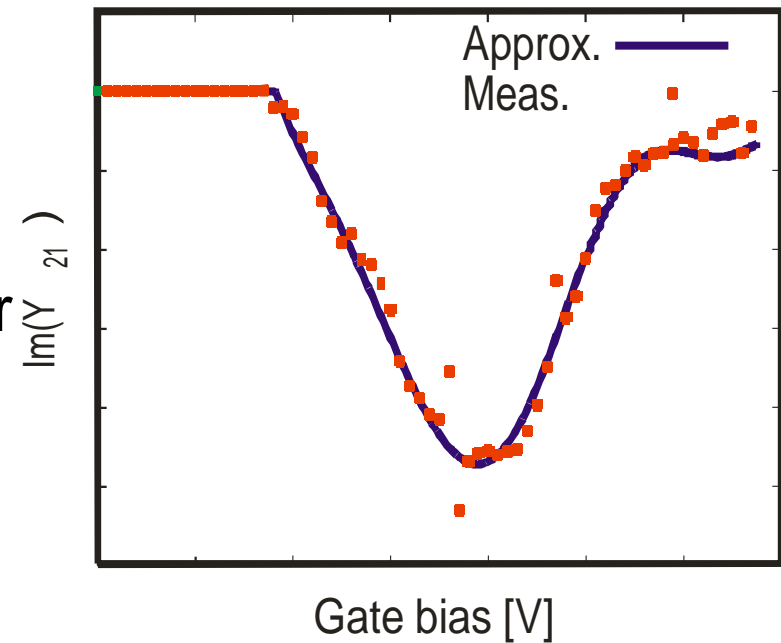
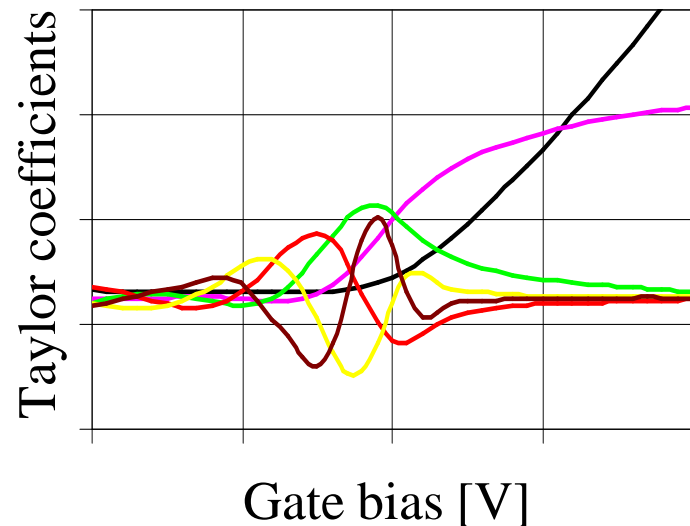
→ No implicit assumptions on the device behavior!

Predictive Modeling & Device Optimization

The database model Smoothie

Advantages of smoothing splines:

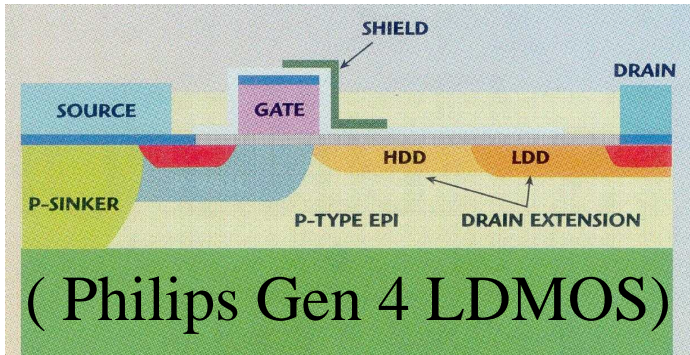
- Immunity to noise
- Smooth derivatives up to 5th order
- Sparse grid



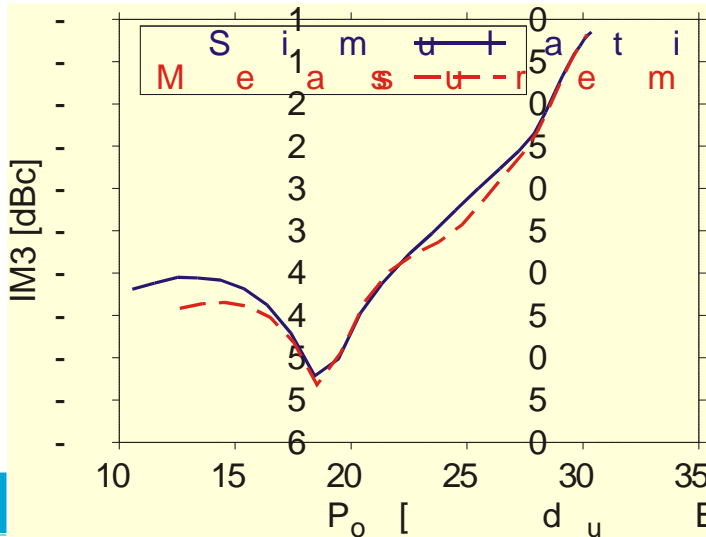
- Reduced extraction time
- Compact model databases

Predictive Modeling & Device Optimization

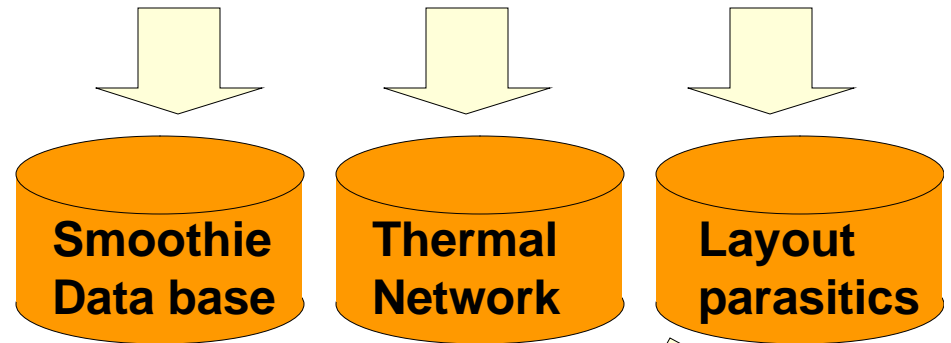
Smoothie used for device engineering



Definition Device Structure



Device simulator (MEDICI)
 Layout extractor (Momentum)
 Thermal network (FEMLAB)



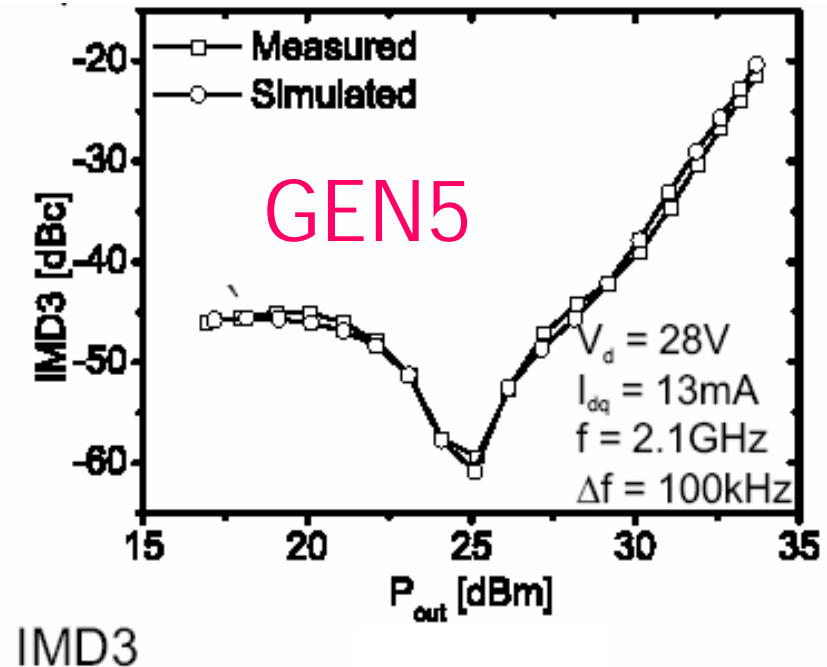
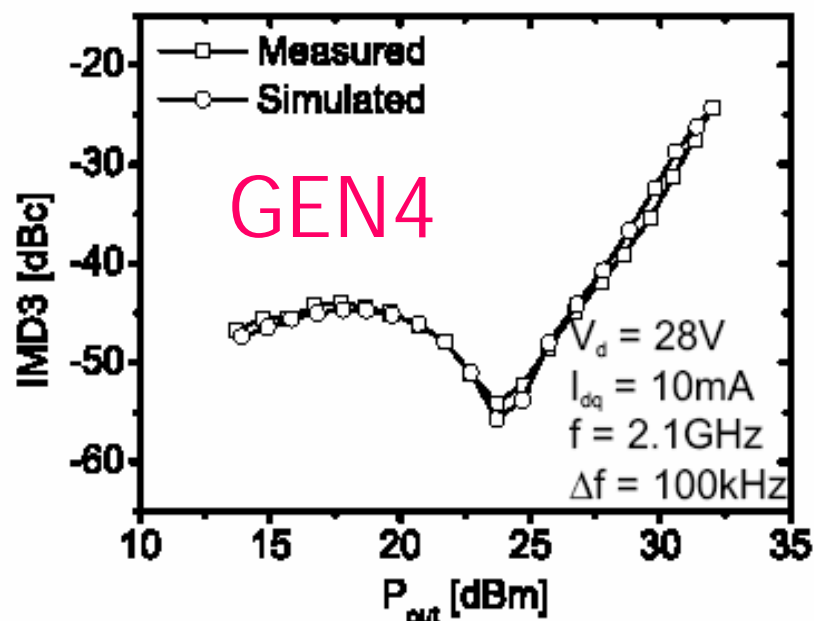
Circuit simulator (ADS)

Predicted and measured LDMOS Linearity!

Predictive Modeling & Device Optimization

Smoothie results

(Figures on courtesy of V. Cuoco and P. Hammes.)

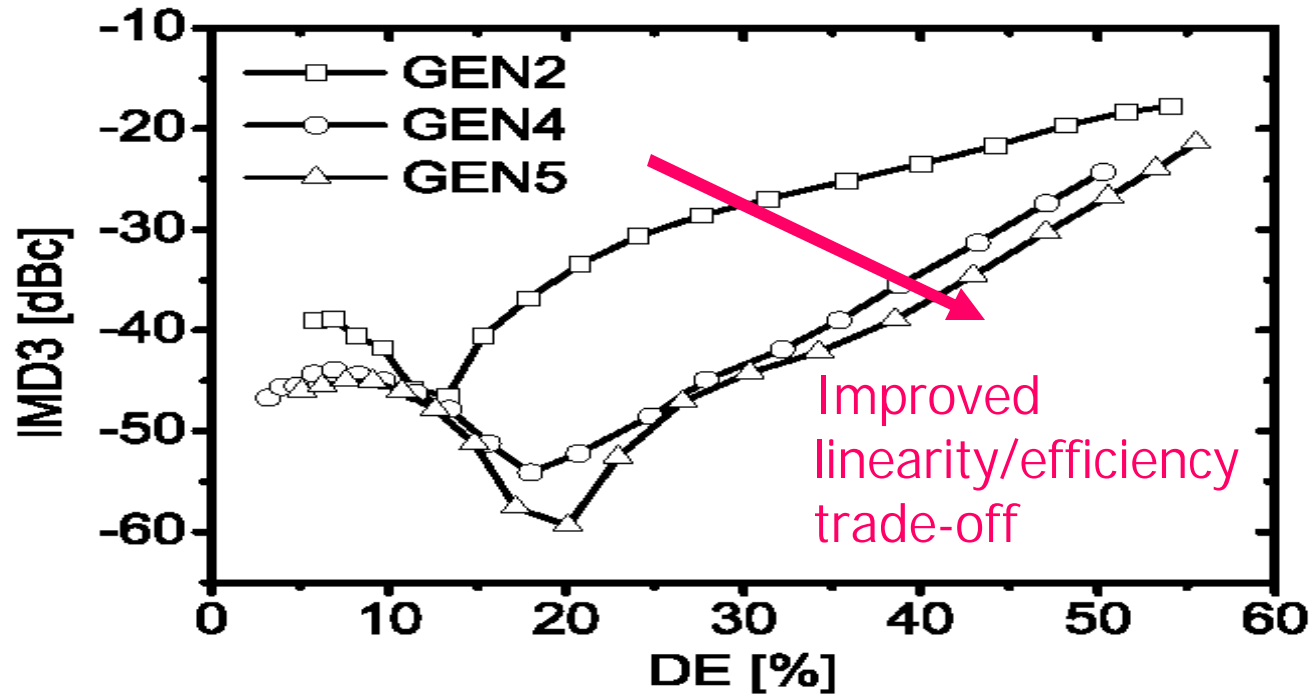


Comparison of **predicted** (Smoothie) and **measured** IM3 for the fabricated Philips LDMOS devices GEN4 and GEN5

Predictive Modeling & Device Optimization

LDMOS Device innovation

(Figure on courtesy of V. Cuoco and P. Hammes.)



Linearity versus efficiency improvements for the Philips LDMOS generations (1-2W devices, on-wafer load-pull measurements).

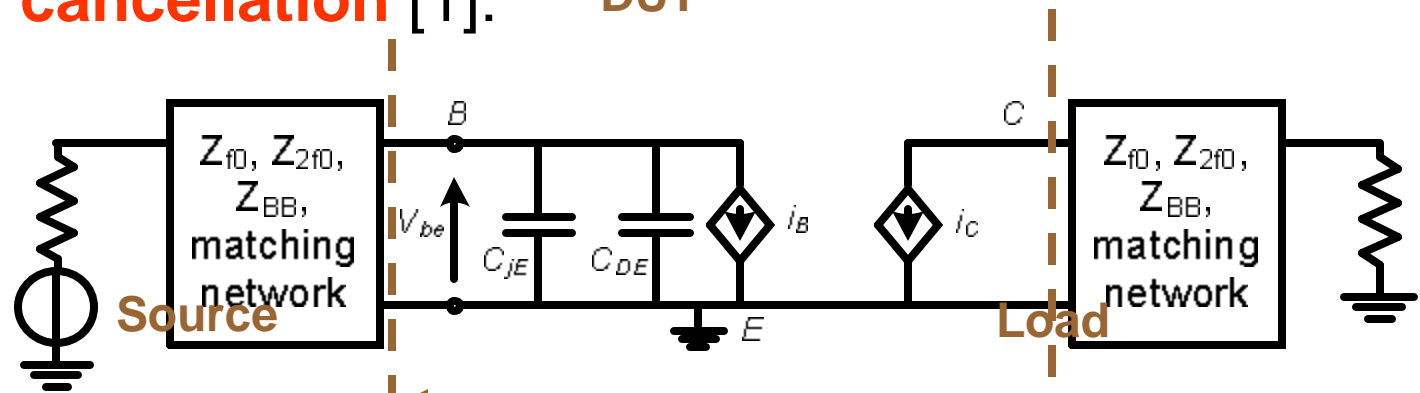
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BJT Based class-AB PA Design

Linearity optimization (theory)

Applying an out-of-band short $Z_{L,BB} = Z_{L,2nd} = 0$ at DUT output simplifies analysis and provides $Z_{S,BB}$ and $Z_{S,2nd}$ to enforce **perfect IM3 cancellation** [1]:



→ **Real part cancellation condition**

$$Z_{S,BB} = Z_{S,2nd} = \frac{\beta_F}{2g_m} \rightarrow \text{Imaginary part cancellation condition}$$

$$C_{jE} = 2g_m \rightarrow \text{Fixed by technology}$$

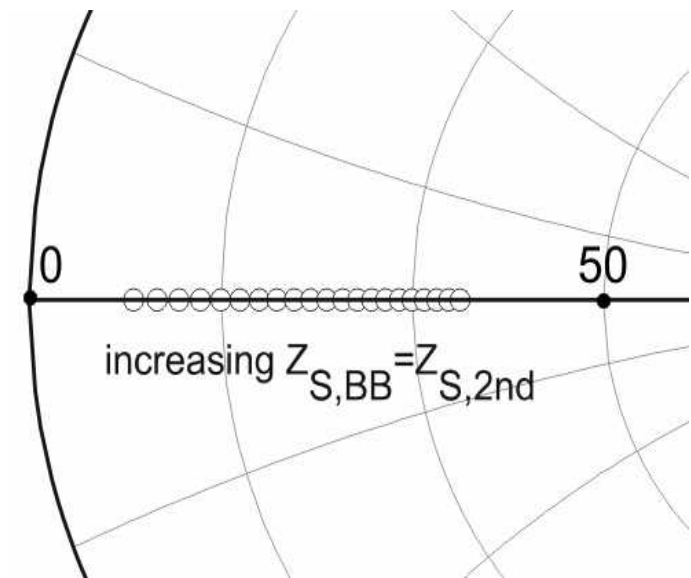
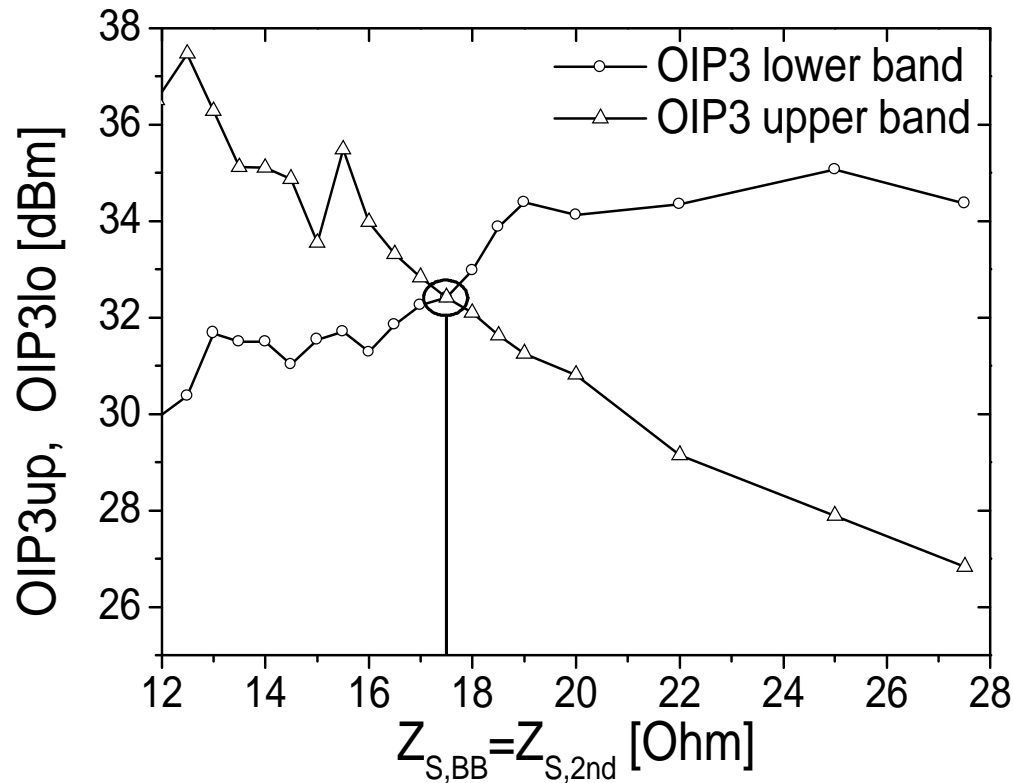
$$I_{c,qpo} \neq T \frac{C_{jE}}{2\tau_F}$$

[1] M.P. van der Heijden et al. BCTM 2004

BJT Based class-AB PA Design

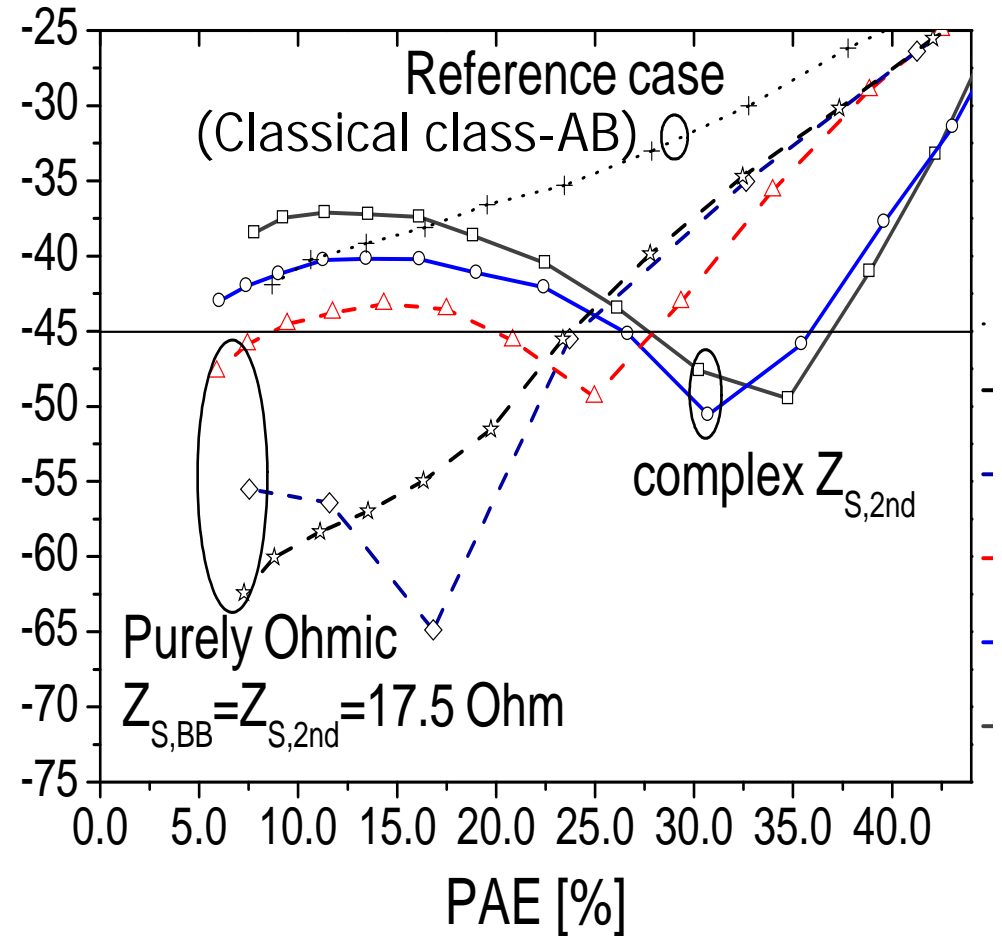
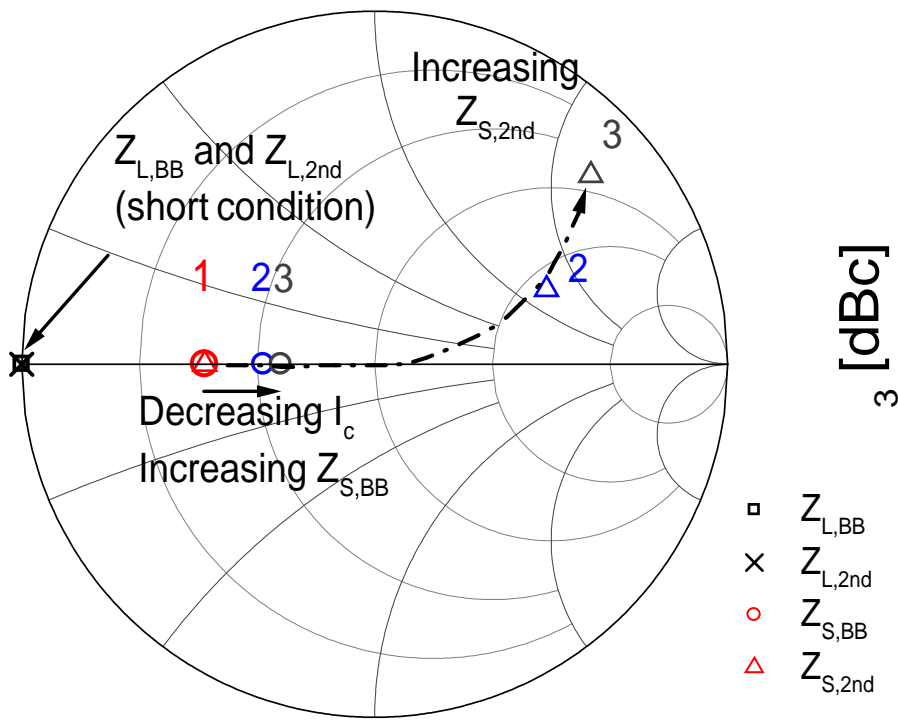
Low-power Linearity opt. (measurement)

By sweeping $Z_{S,BB}=Z_{S,2nd}$ we can experimentally find the symmetrical IM3 cancellation condition, and the related optimal quiescent current I_{cq} .



BJT Based class-AB PA Design

IM3 vs. PAE optimization



	Case 1	Case 2	Case 3
I_{cq}	12 mA	7 mA	6.2 mA
$Z_{S, BB}$	17.5 Ω	26 Ω	29 Ω
$Z_{S, 2nd}$	17.5 Ω	116.5 +68.5 j	38.8 +122.5j

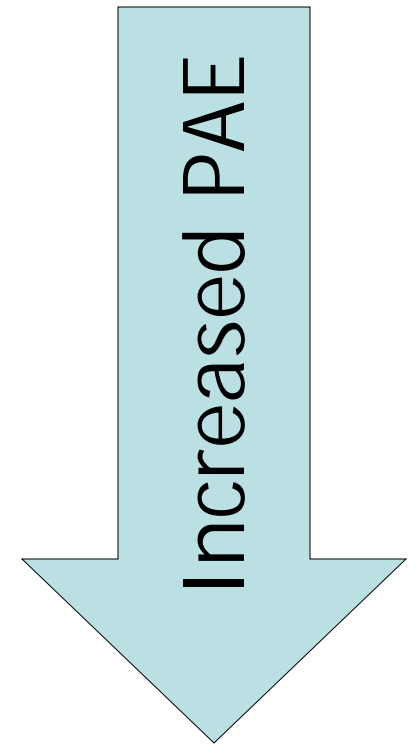
M. Spirito, BCTM 2005

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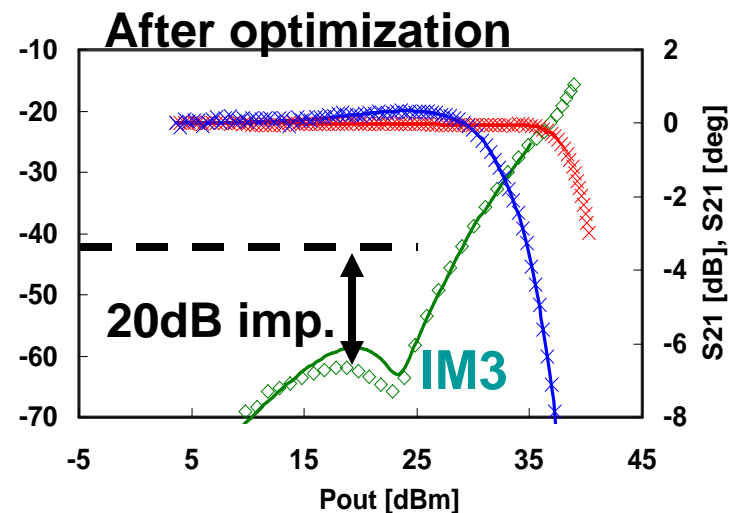
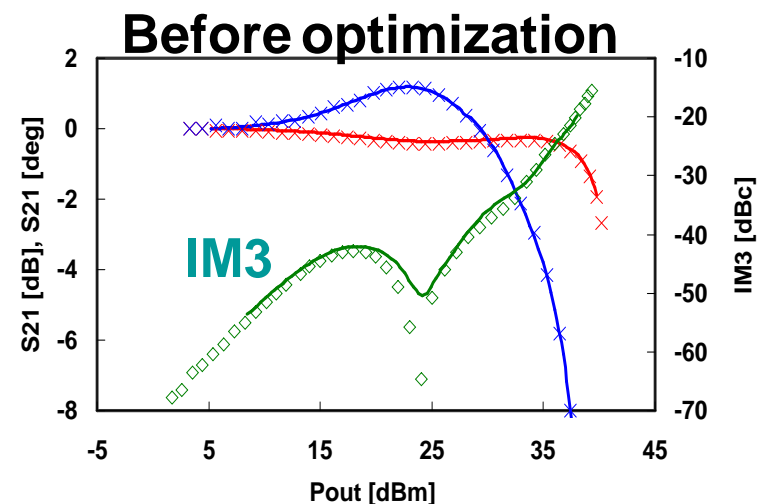
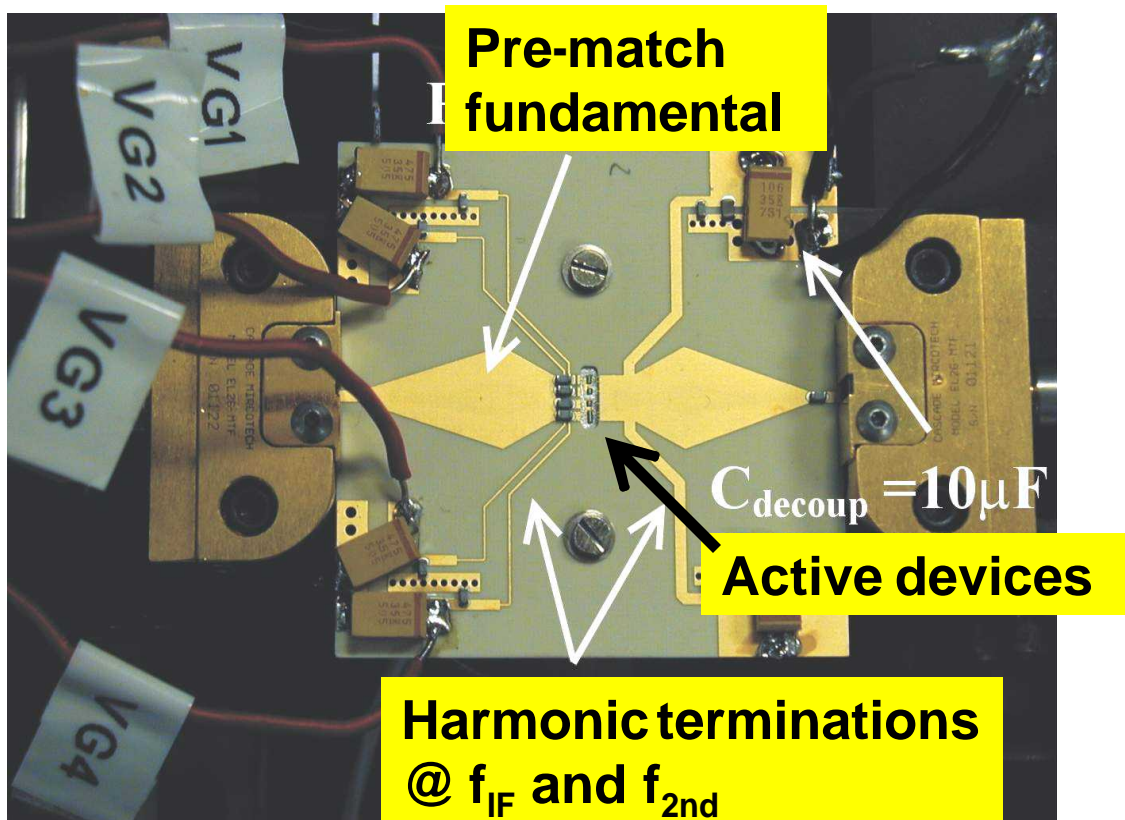
FET Based Design: Lowering $P_{\text{back-off}}$ while still meeting the linearity spec.

- Derivative superposition method
(most effective in back-off region)
[M.v.d. Heijden, IMS2001](#)
- Derivative superposition
+ 2nd harmonic input tuning
(Effective up to close to compression)
[E.W. Neo, EuMC2004](#)
- 2nd harmonic input and output tuning
(Effective up to the compression region)
[D. Hartskeerl, RFIC2005](#)



FET Based Design:

A Square-Law Optimized Class-AB LDMOS Power Amplifier



LDMOS amplifier with trans-conductance shaping using VG-offsets

(M. P. Heijden, Honorable mention at MTT-S2001)

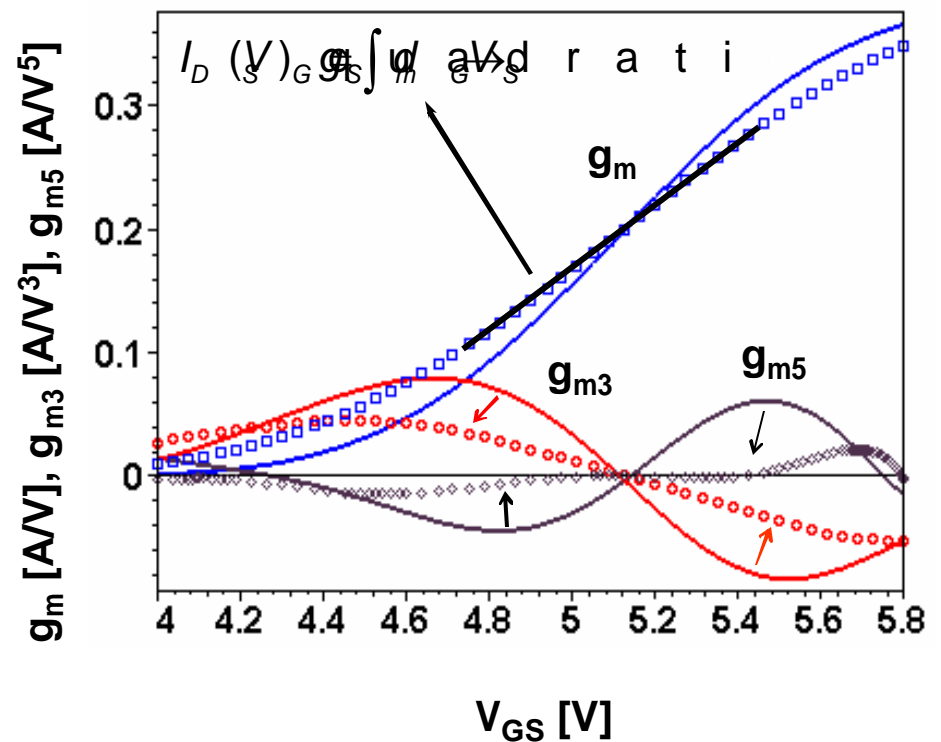
FET Based Design:

A Square-Law Optimized Class-AB LDMOS Power Amplifier

Transconductance Optimization

Linearity optimization by controlling the higher order derivatives of the active device, through:

- V_{gs} offsets (biasing)
- V_T shifts (build-in)

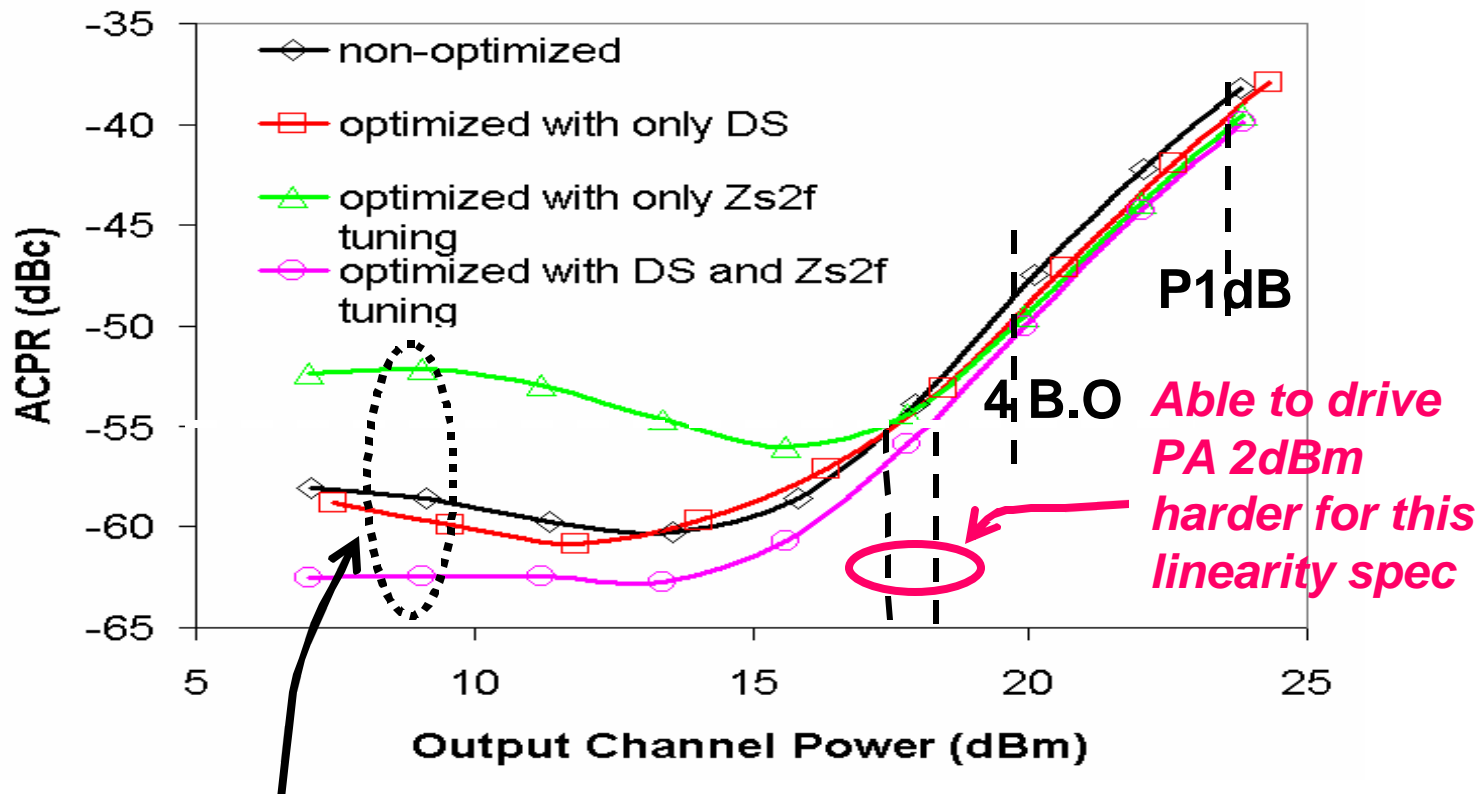


NEW LDMOS generation with build-in optimized Transconductance, introduced at MTT-S 2003

FET Based Design

DS & 2nd Harmonic Input Tuning[#]

- IS-95 CDMA signal on Philips GEN 3 LDMOS



FET Based PA Design

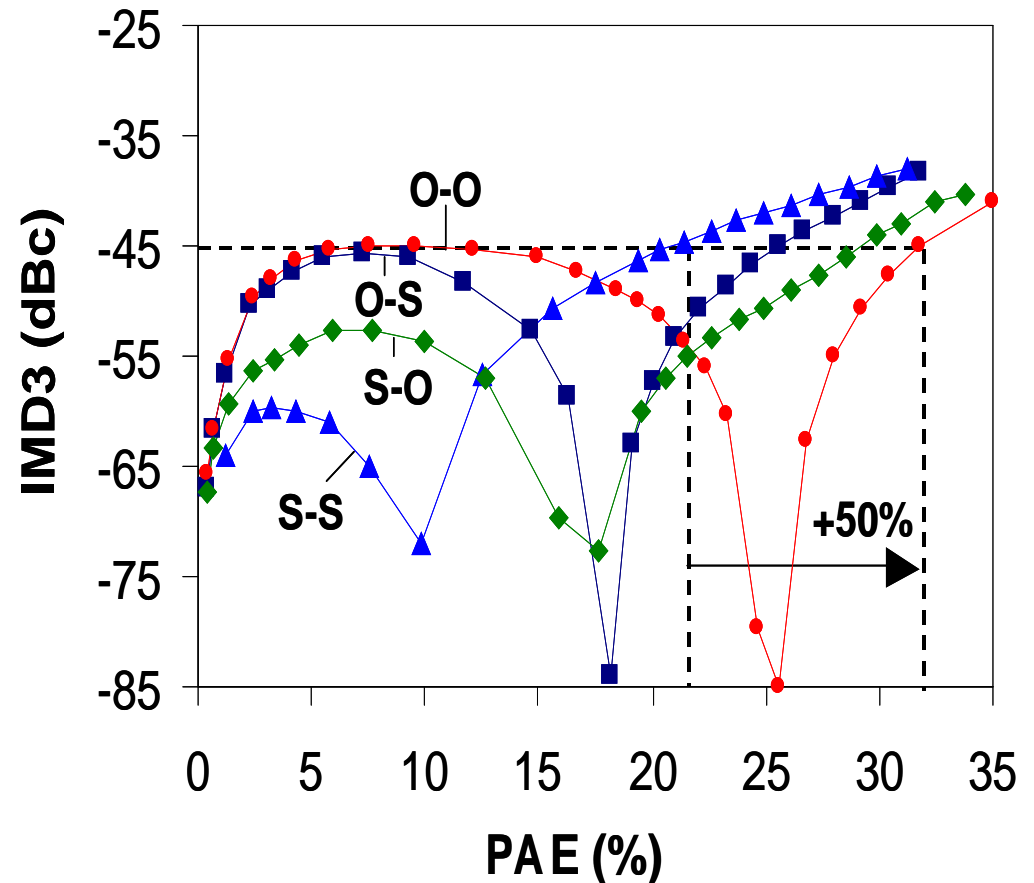
2nd Harmonic input & output tuning

Measured PAE linearity trade-off for 2mm LDMOS device using:

- Open-Short (squares)
- Open-Open (circles)
- Short-Short (triangles)
- Short-Open (diamonds)

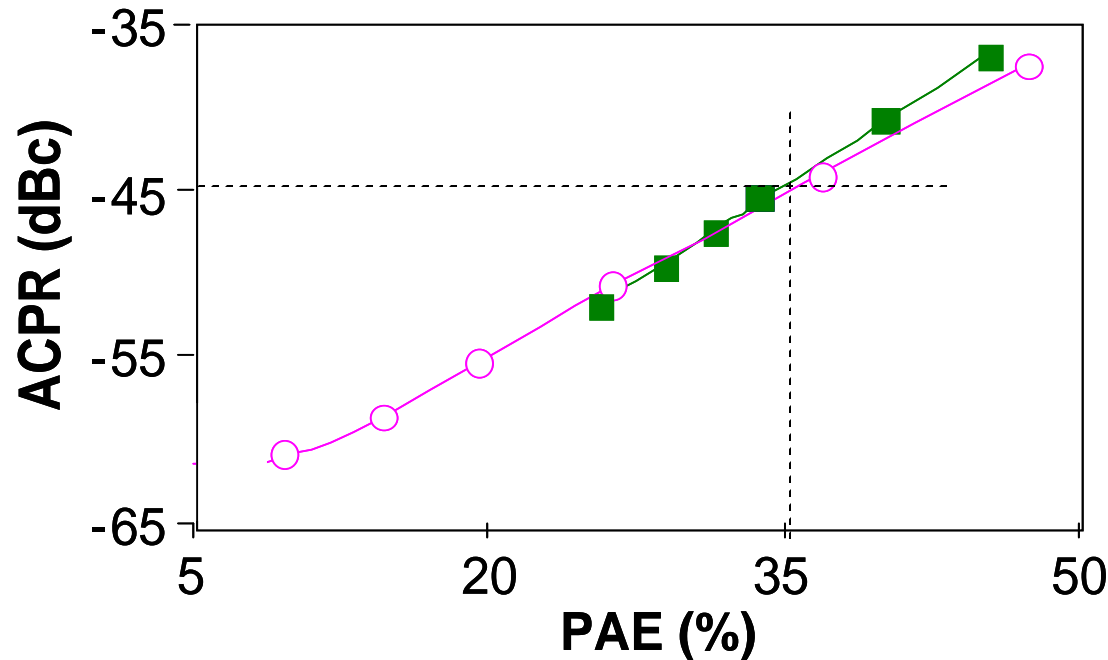
2nd harm. terminations at the device in- and output

(Dave Hartskeerl, RFIC 2005)



FET Based PA Design

2nd Harmonic input & output tuning



Measured using the TUDELFT Active Harmonic Load Pull System

Single carrier IS-95 CDMA signal (open symbols) and single carrier 3GPP WCDMA signal (closed symbols). (D. Hartskeerl, RFIC2005).

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Conclusions

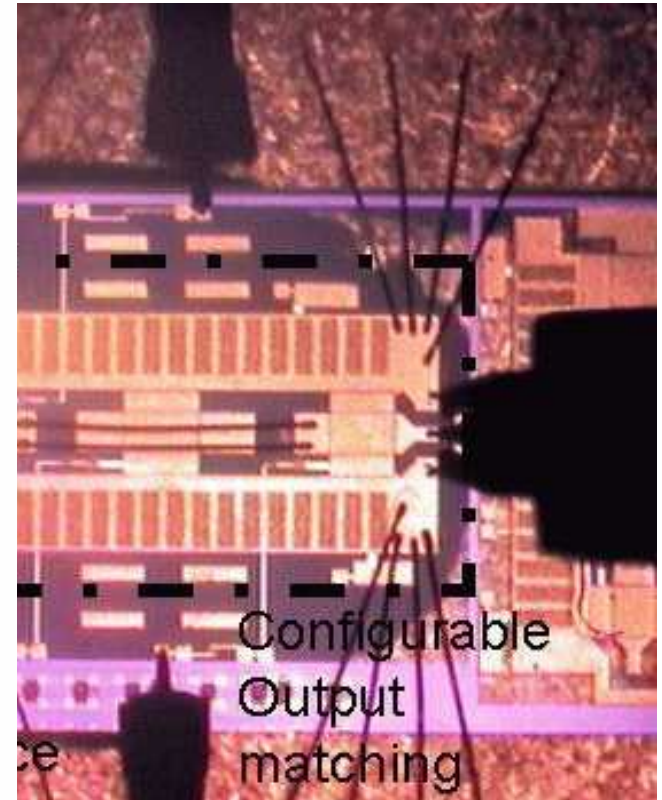
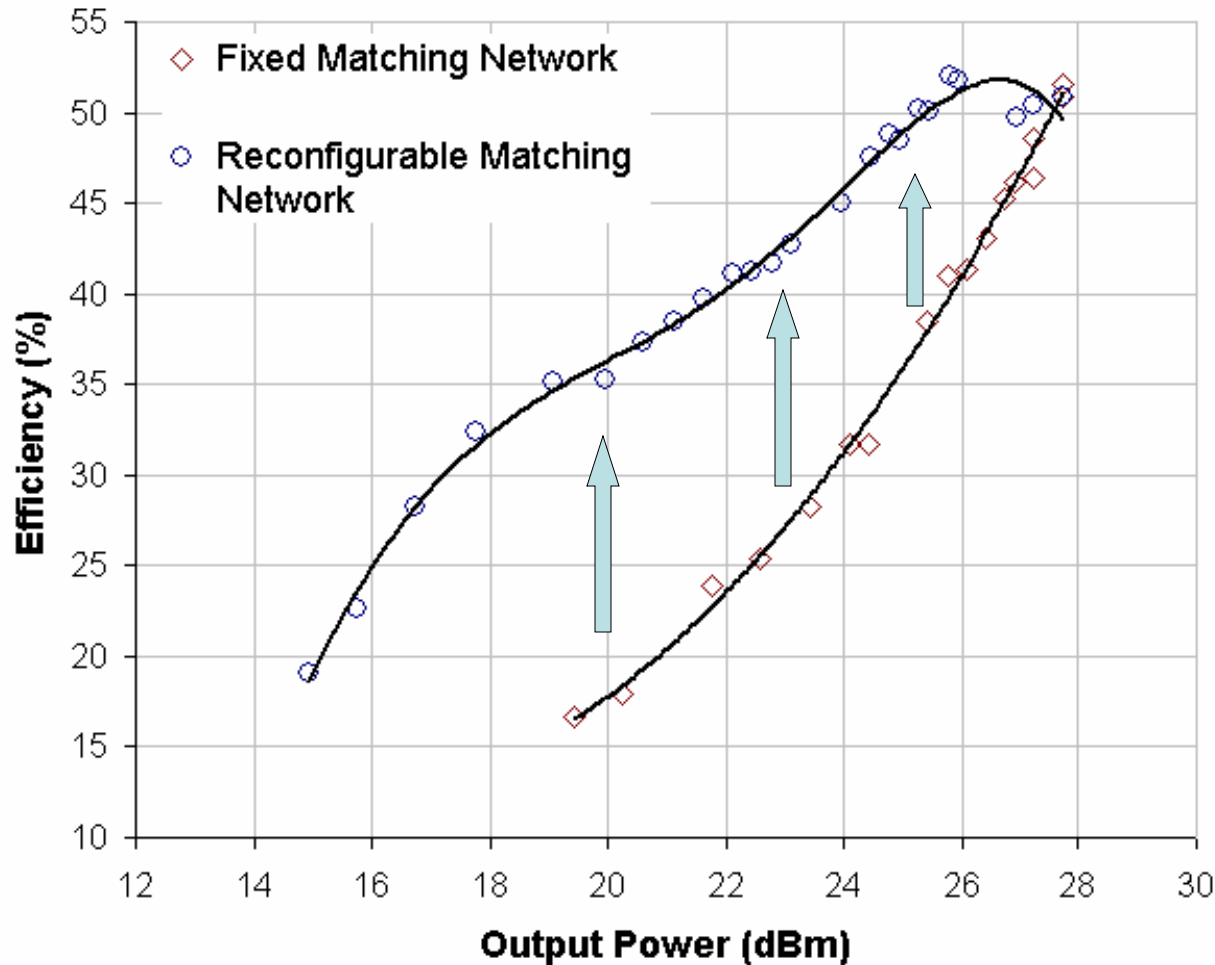
- A research strategy for improve device performance at the TUDelft has been presented, yielding:
 - Unique Measurement equipment
 - Predictive database models
 - Linearity & PAE device optimization strategies
- As result Modified “Class-AB” device operation is still a competitive option for commercial applications providing high linearity performance at a very reasonable PAE level, while being:
 - Low cost,
 - Reliable,
 - Simple.....
- But → Current research fields at the TUDelft also include:
Device and Circuit Innovation for Doherty PA's,
Adaptive / Dynamic Load line PA's, and Polar PA's

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Outlook: Multi-mode, Multi band PA's

High performance varactors for RF adaptivity



Band-switching & Collector efficiency improvement with adaptive matching networks

Acknowledgement

- Philips Semiconductors: R. Jos, P. Lok, F. van Straten P. Hammes, F. v. Rijs, J. Gajadharshing. A. de Graauw, S. Theeuwen
- Philips Research; D. HartsKeerl, Reinout Woltjer
- Infineon: J.E. Muller
- Skyworks: P. Zampardi
- Many people of Agilent, BSW, Maury etc.
- UCSD L. Larson & P. Asbeck

In special (in alphabetic order):

V. Cuoco, M. v.d. Heijden, E. Neo, M. Pelk,
and M. Spirito of the TUDelft.